

REPLACEMENT CLAIMS:

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1. (Amended) A method for forming a semiconductor device structure in a semiconductor layer, comprising:

- forming a first trench of a first width and a second trench of a second width in the semiconductor layer;
- growing a first insulator liner in the first trench and a second insulator liner in the second trench;
- forming a mask over the second trench;
- etching at least a portion of the first insulator liner while the mask is over the second trench;
- removing the mask; and
- depositing an insulating layer in the first trench and the second trench.

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5. (Amended) The method of claim 1, wherein the step of growing the first insulator liner and the second insulator liner comprises growing oxide in the first trench and the second trench.

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15. (Amended) A method for forming a semiconductor device structure in a semiconductor layer, comprising:

- forming a first trench of a first width and a second trench of a second width in the semiconductor layer, the first width being less than the second width;
- growing a first insulator liner in the first trench and a second insulator liner in the second trench;
- forming a mask over the second trench; and
- etching at least a portion of the first insulator liner while the mask is over the second trench.

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19. (Amended) The method of claim 15, wherein the step of growing the first insulator liner and the second insulator liner comprises growing oxide in the first trench and the second trench.

20. (Amended) The method of claim 15, wherein:

the semiconductor layer has a top surface;
the second trench has a corner where the trench adjoins the top surface of the semiconductor layer; and
the step of growing the first insulator liner and the second insulator liner comprises rounding of the corner of the second trench.

26. (Amended) A method for forming a semiconductor device structure in a semiconductor layer, comprising:

forming a first trench of a first width in the semiconductor layer;
forming a second trench of a second width greater than the first width in the second semiconductor layer;
growing a first insulator liner in the first trench and a second insulator liner in the second trench;
etching a portion of the first insulator liner; and
depositing an insulating layer in the first trench.

29. (Amended) A method for forming a semiconductor device structure in a semiconductor layer, comprising:

forming a first trench of a first width in the semiconductor layer;
forming a second trench of a second width in the second semiconductor layer;
growing a first insulator liner in the first trench and a second insulator liner in the second trench;
etching a portion of the first insulator liner and a portion of the second insulator liner; and
depositing an insulating layer in the first trench and the second trench.